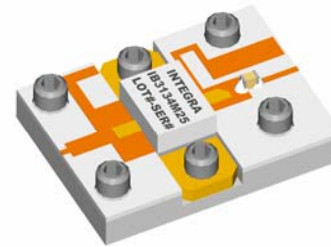


S-Band Radar Transistor

Part number IBP3134M25 is a 50 Ω matched high power pulsed radar pallet amplifier for S-Band radar systems operating over the instantaneous bandwidth of 3.1-3.4 GHz. Operating under the pulse conditions of 300µs pulse width and 10% duty cycle the pallet amplifier supplies a minimum of 25 watts of peak power over the frequency range of 3.1-3.4GHz. All devices are 100% screened for large signal RF parameters.



- Silicon Bipolar Technology
 - Ultra-high f_T
- Class C Operation
 - High Efficiency
- Common Base Configuration
 - Single Power Supply
- Gold Metal
 - Maximum Reliability
- Emitter Ballasting
 - Optimum Thermal Distribution
- Impedance Matched to 50Ω
 - Ease of Use
- Pallet Carrier
 - Ni Plated Cu Carrier
- BeO Based Transistor Package
 - Unmatched Thermal Reliability

TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

Device	Freq (MHz)	V _{CC} (V)	P _{IN} (W)	IRL (dB)	P _{OUT} (W)	G _P (dB)	I _c (A)	N _c (%)	Droop (dB)
506445-2	3100	32.0	2.6	-18	33.7	11.1	2.10	50	-0.2
	3250	32.0	2.6	-18	33.1	11.1	2.10	49	-0.2
	3400	32.0	2.6	-24	30.6	10.7	2.10	45	-0.1

Pulse Format = 300µs, 10%

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	V_{CES}	--	70	V	$V_{BE}=0V$.
BD	Emitter-Base Voltage	V_{EBO}	--	3.5	V	--
BD	Storage Temperature Range	T_{STG}	-55	+150	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

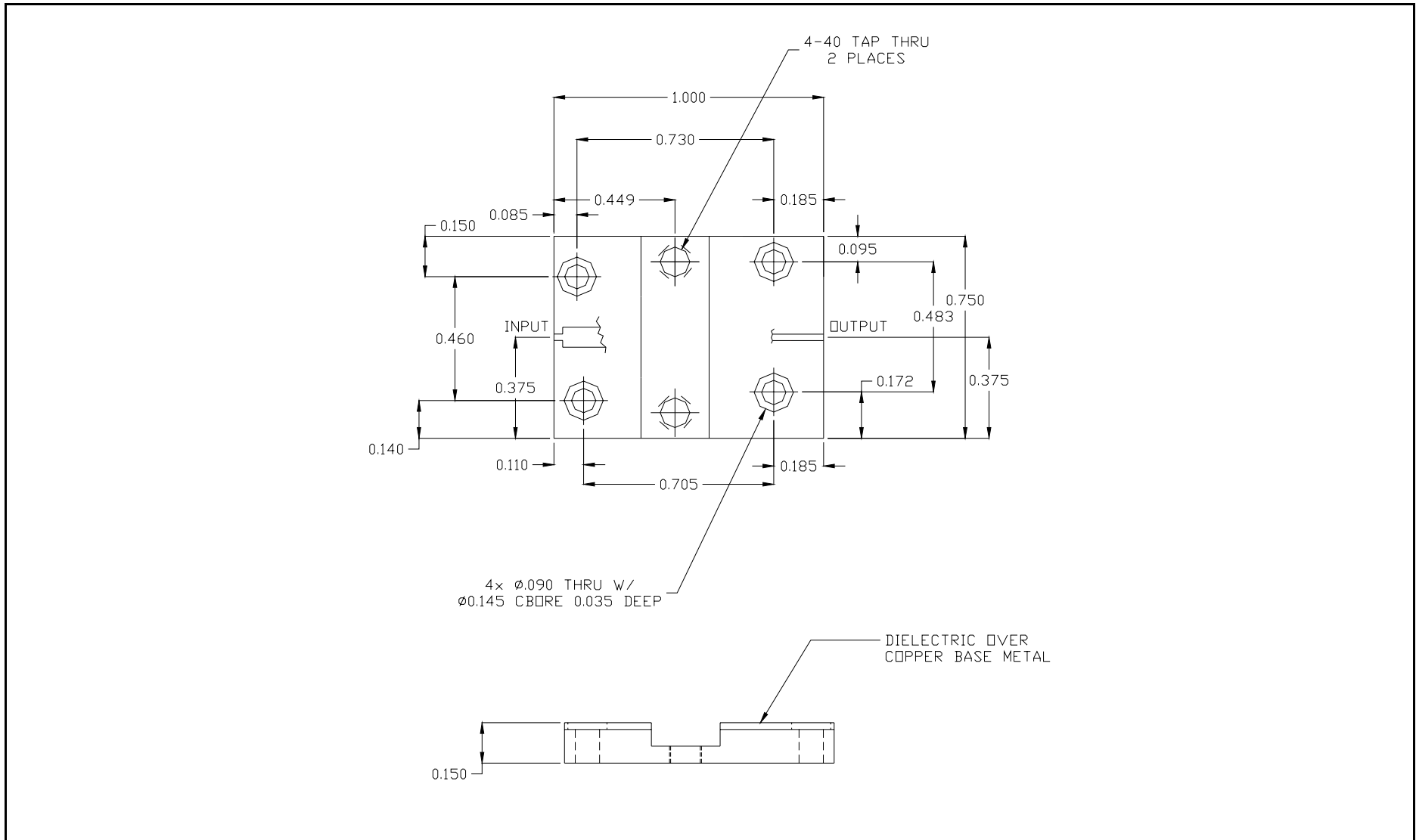
THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance per Device	$R_{TH(JC)}$	--	1.45	°C/W	$V_{CC}=V1$, $PW=PW1$, $DF=DF1$, $T_F=25\pm5^\circ C$, $P_{OUT}= 25W$, $F=F3$, Per transistor.
Note	Screen 'BD' = parameter qualified By Design.					

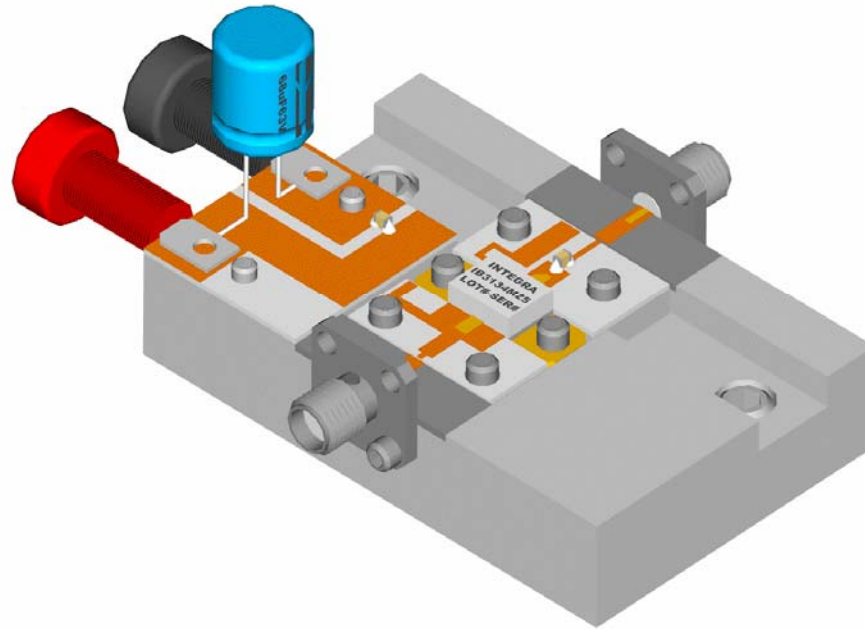
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	10	--	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN}, F=F1, F2, F3.$
100%	Output Power	P_O	25	--	W	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN}, F=F1, F2, F3.$
100%	Collector Efficiency ($P_O/I_C/V_{CC}$)	N_C	40	--	%	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN}, F=F1, F2, F3.$
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN}, F=F1, F2, F3.$
100%	Output Power Compression = $10 \cdot \text{LOG}(P_{OC}/P_O)$	OPC	-0.2	+0.70	dB	P_{OC} measured with P_{IN} increased by 0.5dB at $F=F1, F2, F3.$
100%	Output Power Flatness = $10 \cdot \text{LOG}(P_{OMAX}/P_{OMIN})$	OPF	--	1.0	dB	Calculate from P_O at each frequency F.
100%	Stability into 1.5:1 VSWR	VSWR-S	--	--	--	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN}, F=F1, F2, F3.$ Rotate 1.5:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	2:1 Load Mismatch Tolerance	LMT	--	--	--	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN}, F=F1, F2, F3.$ Rotate 2:1 output VSWR through 360° phase.
BD	Pulse Risetime	RT	--	150	ns	$V_{CC}=V1, PW=PW1, DF=DF1, T_F=25\pm5^\circ C, P_{IN}=P_{IN}, F=F1, F2, F3.$ Measure between 10% and 90% detected power points.
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Note	$V1 = 32V; PW1 = 300\mu s; DF1 = 10\%; P_{IN} = 2.6W; F1 = 3.10 \text{ GHz}, F2 = 3.25 \text{ GHz}, F3 = 3.40 \text{ GHz}.$					
Note	$T_F =$ Device flange temperature. Screen 'BD' = parameter qualified By Design.					

PALLET DIMENSIONAL OUTLINE DRAWING



50Ω RF TEST FIXTURE



HEATSINK NOT SHOWN
DRAWINGS AVAILABLE UPON REQUEST

DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only and operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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